

DSA2401

Silicon PNP epitaxial planar type

For low frequency amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-15	V
Collector-emitter voltage (Base open)	V_{CEO}	-10	V
Emitter-base voltage (Collector open)	V_{EBO}	-7	V
Collector current	I_C	-0.5	A
Peak collector current	I_{CP}	-1	A
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Package

- Code
Mini3-G3-B-B
- Pin Name
 1. Base
 2. Emitter
 3. Collector

■ Marking Symbol: B1

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

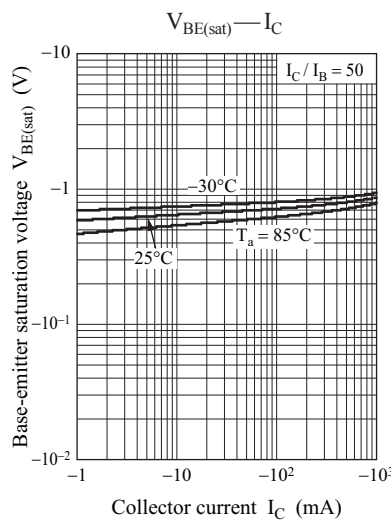
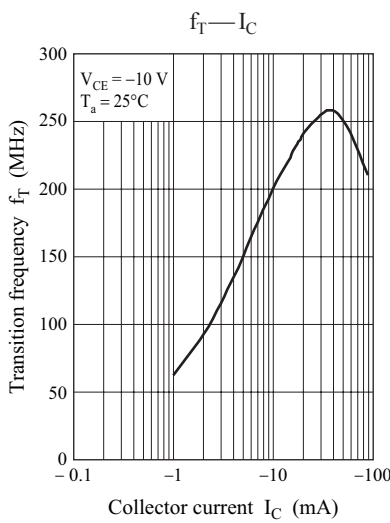
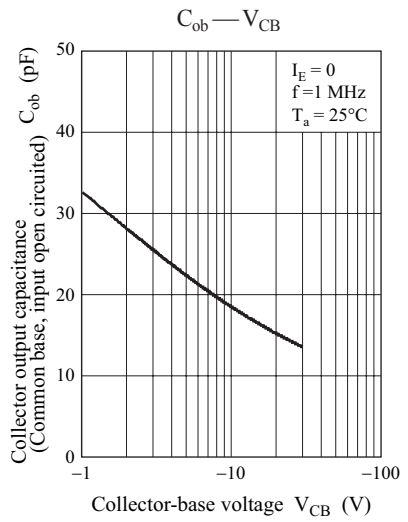
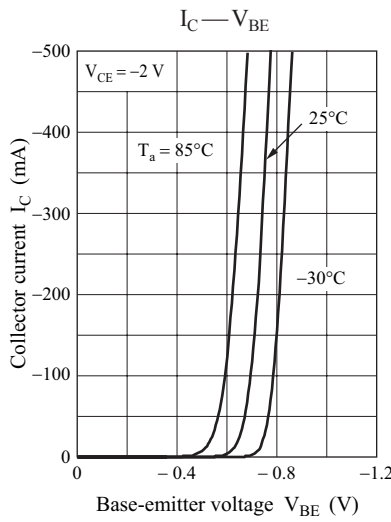
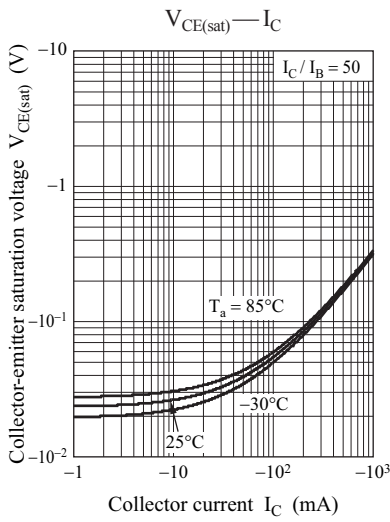
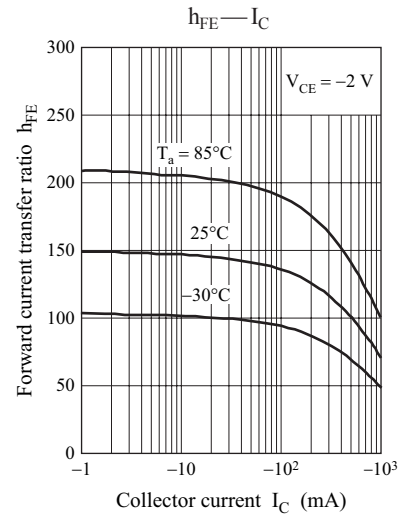
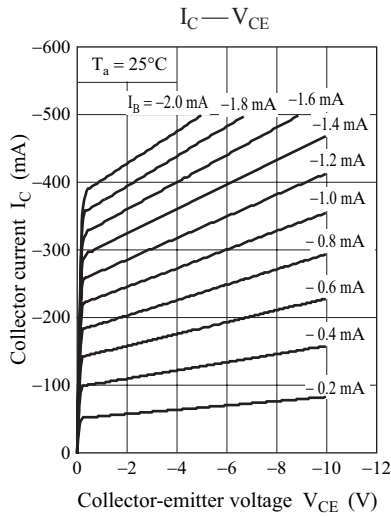
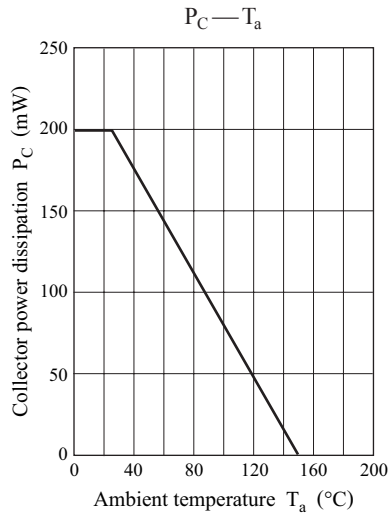
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-15			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-10			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-100	μA
Forward current transfer ratio *1	h_{FE1} *2	$V_{CE} = -2 \text{ V}, I_C = -0.5 \text{ A}$	130		350	—
	h_{FE2}	$V_{CE} = -2 \text{ V}, I_C = -1 \text{ A}$	60			
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -0.4 \text{ A}, I_B = -8 \text{ mA}$		-0.15	-0.30	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = -0.4 \text{ A}, I_B = -8 \text{ mA}$		-0.8	-1.2	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -50 \text{ mA}$		250		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		18		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

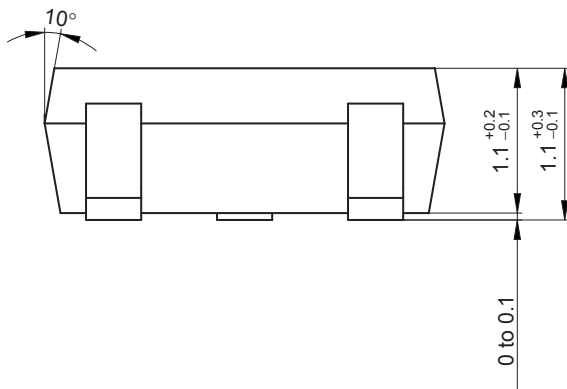
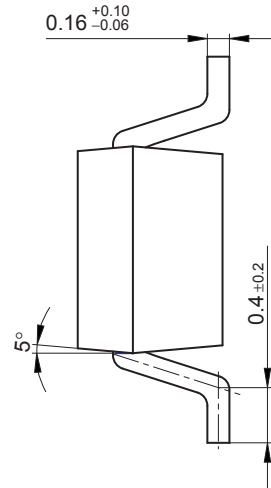
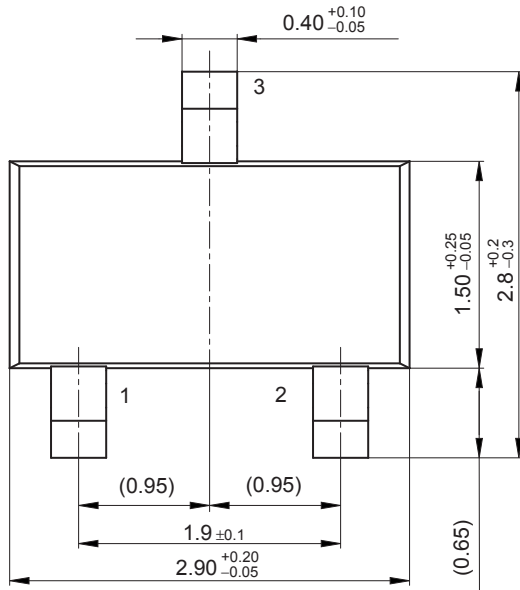
*2: Rank classification

Code	R	S
Rank	R	S
h_{FE1}	130 to 220	180 to 350
Marking Symbol	B1R	B1S



Mini3-G3-B-B

Unit: mm



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